

10/565624**AP20 Rec'd PCT/PTO 24 JAN 2006****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re U.S. Patent Application of)
SUDA et al.)
Application Number: To Be Assigned)
Filed: Concurrently Herewith)
For: FIELD EFFECT TRANSISTOR AND METHOD FOR)
MANUFACTURING SAME)
ATTORNEY DOCKET NO. HIRA.0217)

Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified National Stage U.S. patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each foreign patent, or each publication or portion thereof listed or herein identified, is submitted herewith.

CERTIFICATION

This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /S.A./

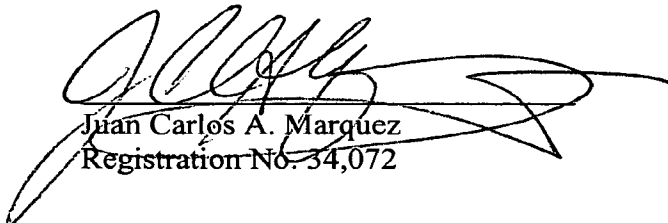
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Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER HIRA.0217	SERIAL NUMBER To be Assigned 10/565.624
	APPLICANT SUDA et al.	
	FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	5,900,648	5/4/99	Harris et al.			3/28/97

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						Yes	No
	2000-150792	11/11/98	Japan			Abstract	X
	2001-094099	9/21/99	Japan			Abstract	X
	2002-246594	12/21/2001	Japan			Abstract	X
	FR 2 707 425	7/9/93	France			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

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EXAMINER /Selim Ahmed/	DATE CONSIDERED 12/22/2008
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